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oxide which can be thermally grown or deposited such as by chemical vapor deposition or physical vapor deposition. Typically, the insulating layer is about 2000 to about 30,000 Å thick, and more typically about 4000 to about 20,000 Å thick.

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According to an alternative process according to the present invention, recesses 2 such as troughs and vias are provided on at least one major surface of a semiconductor substrate 13. Electrical insulation 3 is provided over the major surface and in the recesses such as silicon dioxide which can be thermally grown or deposited such as by chemical vapor deposition or physical vapor deposition. Typically, the insulating layer is about 2000 to about 30,000 Å thick, and more typically about 4000 to about 20,000 Å thick.

IN THE CLAIMS:

Please amend the claims as follows:

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25. (Amended) A semiconductor structure comprising a semiconductor substrate; recesses located in at least one major surface of said semiconductor substrate; electrical insulating layer located at least one major surface over said at least one major surface and in said recesses; a conductive barrier located over said insulating layer in said recesses and over said at least one major surface; a plating seed layer located over said conductive barrier within said recesses only; and an electroplated conductive metal in said recesses only.

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30. (Amended) The semiconductor structure of claim 28 wherein said copper is about 100 to about 2000 Å thick.